



Features

- Phase Shift Accuracy RMS: 1.3 °
- Insertion Loss: 6dB (Typ.)
- Insertion Loss Variation: 1dB
- Impedance: 50Ω
- Die Size: 4 x 1.61 x 0.1 mm

Typical Applications

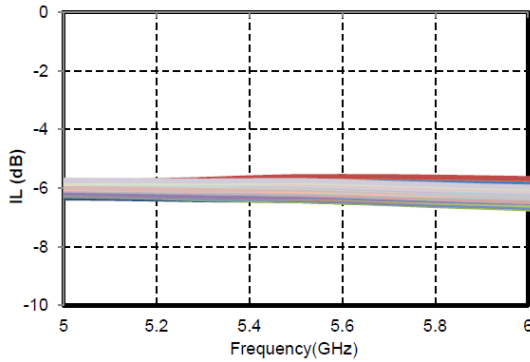
- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

Electrical Specifications

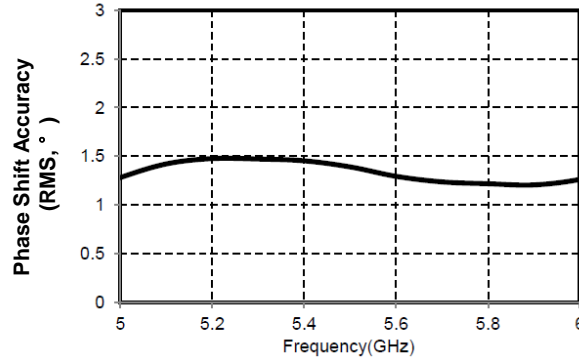
TA = +25°C, Vctl = 0/-5V

Parameters	Min.	Typ.	Max.	Units
Frequency		5-6		GHz
Insertion Loss		6.0	7.0	dB
Insertion Loss Variation		±0.5		dB
Phase Shift Accuracy RMS		1.3		°
Amplitude Variation		1.3		dB
Input Return Loss	13	18		dB
Output Return Loss	14	21		dB
Switching Speed		20		ns

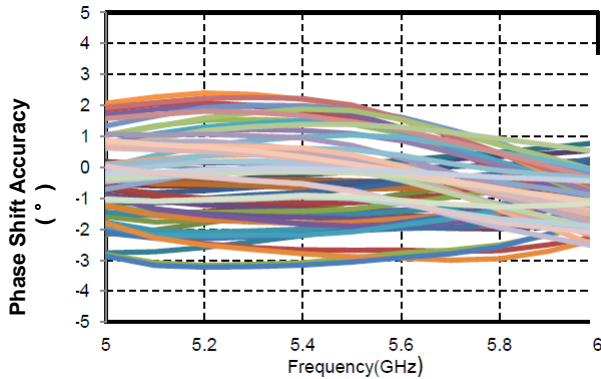
Insertion Loss



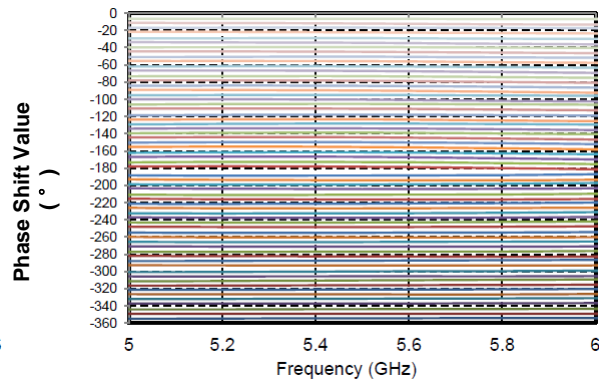
Phase Shift Accuracy (RMS)



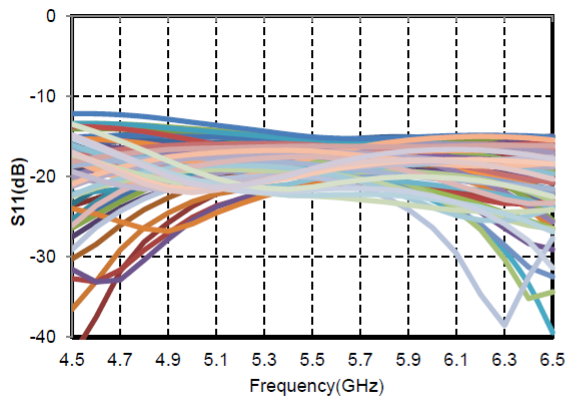
Phase Shift Accuracy



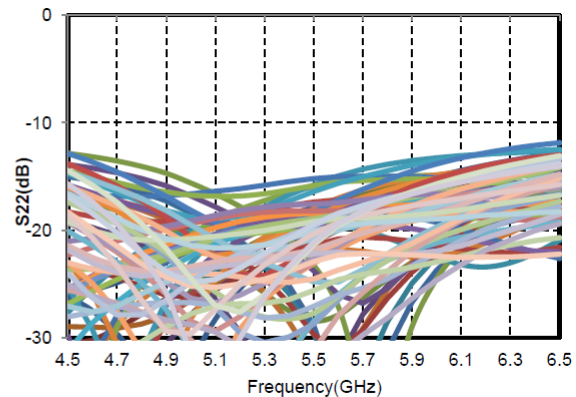
Phase Shift Value

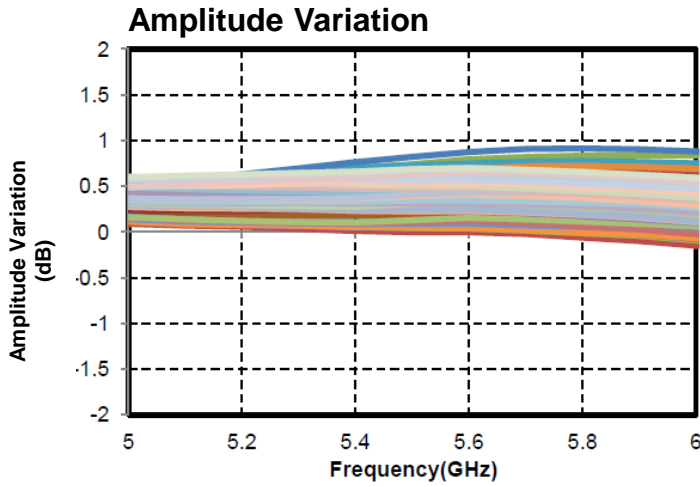


Input Return Loss

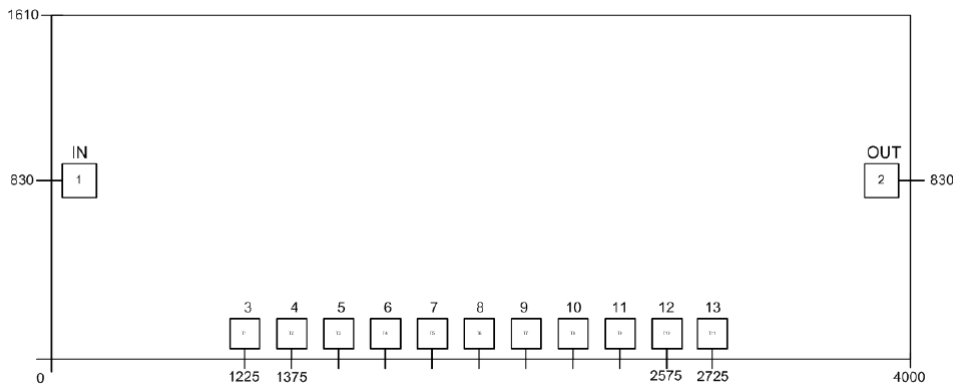


Output Return Loss





Outline Drawing: All Dimensions in μm



Pad Description

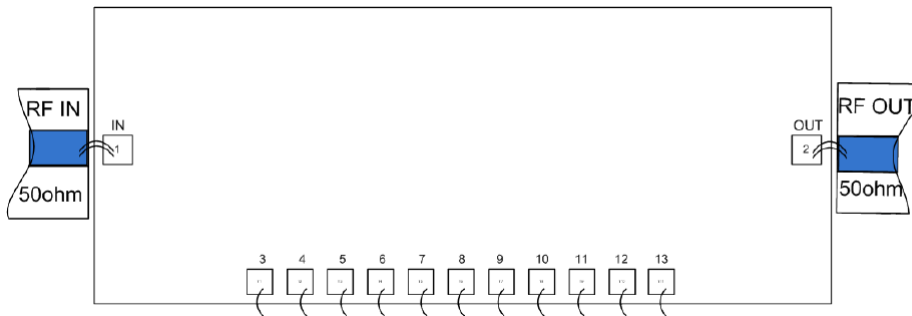
PAD	Function	Description
1	RF IN	RF Input Port
2	RF OUT	RF Output Port
3-13	CTRL	Control Port
GND	GND	Die bottom must be connected to RF/DC ground



Truth Table

	T1	T2	T3	T4	T5	T6	T7	T8	T9	T10	T11
0	-5	0	-5	-5	0	-5	0	0	-5	0	-5
5.625	-5	0	0	-5	0	-5	0	0	-5	0	-5
11.25	-5	0	-5	-5	0	0	-5	0	-5	0	-5
22.5	-5	0	-5	-5	0	-5	0	-5	0	0	-5
45	-5	0	-5	0	-5	-5	0	0	-5	0	-5
90	-5	0	-5	-5	0	-5	0	0	-5	-5	0
168.75	-5	0	-5	0	-5	0	-5	-5	0	-5	0
174.375	-5	0	0	0	-5	0	-5	-5	0	-5	0
180	0	-5	-5	-5	0	-5	0	0	-5	0	-5
354.375	0	-5	0	0	-5	0	-5	-5	0	-5	0

Assembly Drawing



Notes:

1. Die thickness: 100um
2. Typical bond pad is 100*100 μm²
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:

1. RF input power: +23dBm
2. Control voltage range: -8V~0.5V
3. Storage temperature: -65°C to +150°C
4. Operating temperature: -55°C to +85°C